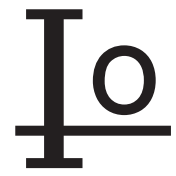


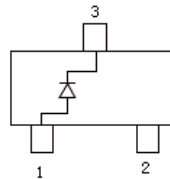
BAS20

SWITCHING DIODE

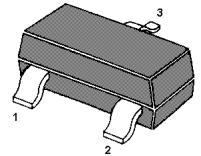


FEATURES

- Fast Switching Speed
- Surface Mount Package Ideally Suited for Automatic Insertion
- For General Purpose Switching Applications
- High Conductance



SOT-23



Marking: JR

Maximum Ratings @T_A=25°C

Parameter	Symbol	Limits	Unit
Non-Repetitive Peak reverse voltage DC Blocking Voltage	V _{RM} V _R	150	V
Average Rectified Output Current	I _o	200	mA
Power Dissipation	P _d	250	mW
Thermal Resistance. Junction to Ambient Air	R _{θJA}	500	°C/W
Junction temperature	T _J	150	°C
Storage temperature range	T _{STG}	-65-150	°C

ELECTRICAL CHARACTERISTICS (T_{amb}=25°C unless otherwise specified)

Parameter	Symbol	Test conditions	MIN	MAX	UNIT
Reverse breakdown voltage	V _{(BR)R}	I _R = 100μA	150		V
Reverse voltage leakage current	I _R	V _R =150V		0.1	μA
Forward voltage	V _F	I _F =100mA I _F =200mA		1 1.25	V
Junction Capacitance	C _J	V _R =0V, f=1MHz		5	pF
Reveres recovery time	t _{rr}	I _F =I _R =30mA, I _{rr} =0.1×I _R		50	nS

Typical Characteristics

BAS20

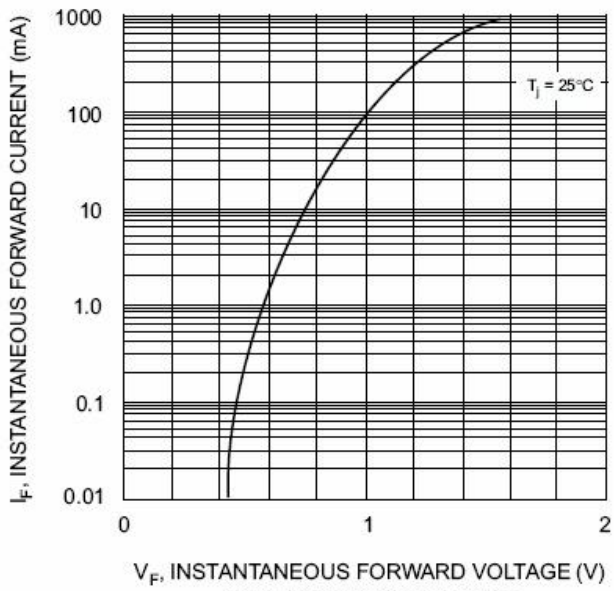


Fig. 1 Forward Characteristics

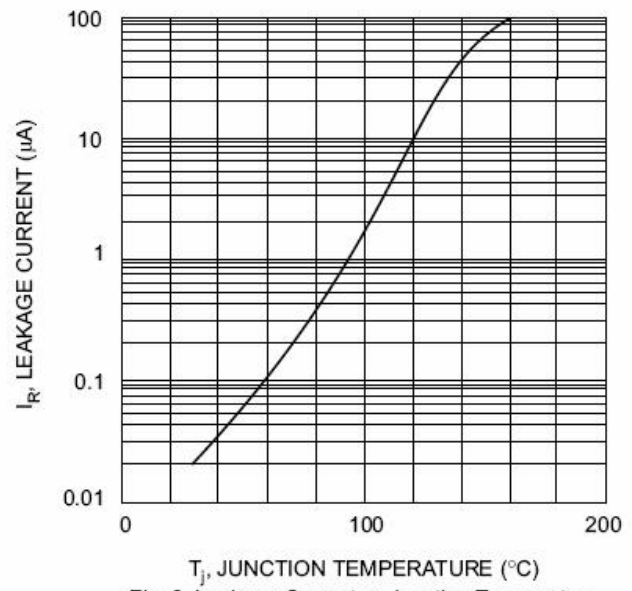
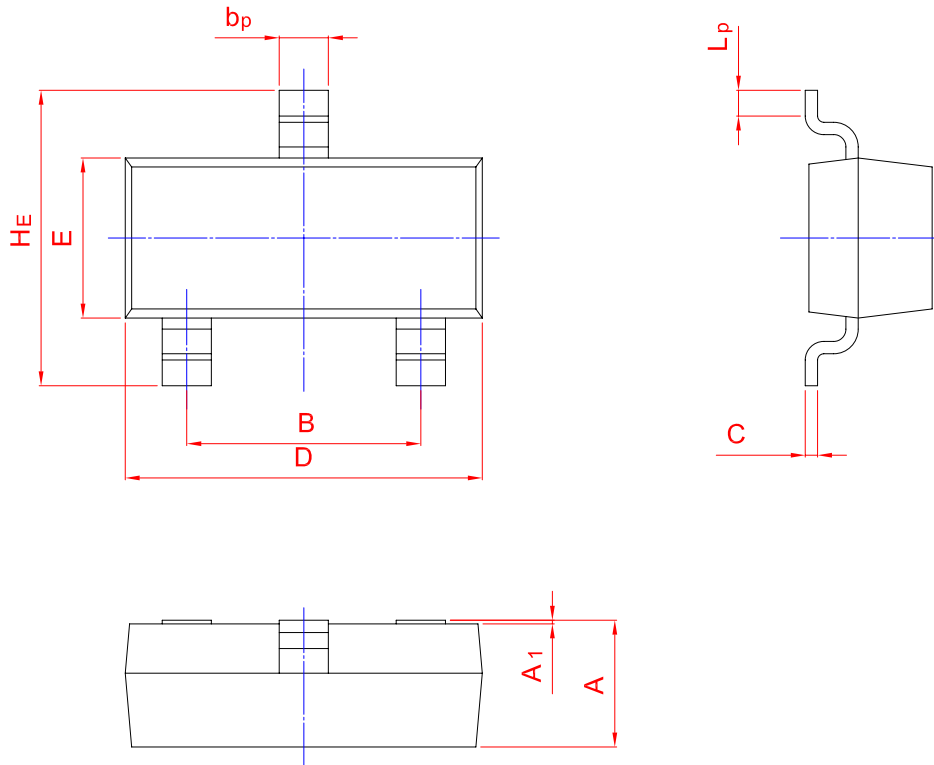
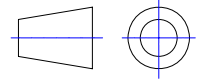


Fig. 2 Leakage Current vs Junction Temperature

PACKAGE OUTLINE

Plastic surface mounted package; 3 leads

SOT-23



UNIT	A	B	b _p	C	D	E	H _E	A ₁	L _p
mm	1.40	2.04	0.50	0.19	3.10	1.65	3.00	0.100	0.50
	0.95	1.78	0.35	0.08	2.70	1.20	2.20	0.013	0.20